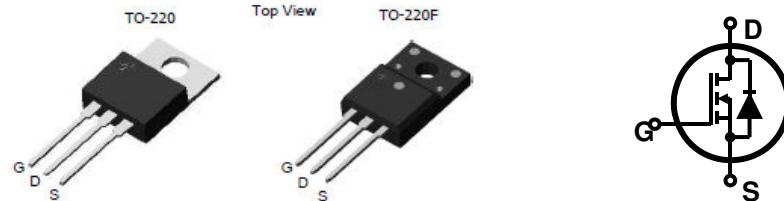


N-channel MOSFET

BV_{DSS}	I_D	$R_{DS(on)}$
500V	8.5A	<0.85Ω

Features

- Low gate charge
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant
- Halogen free package
- JEDEC Qualification



Device	Package	Marking	Remark
GP1M009A050HS	TO-220	GP1M009A050HS	RoHS
GP1M009A050FSH	TO-220F	GP1M009A050FSH	Halogen Free

Absolute Maximum Ratings

Parameter	Symbol	GP1M009A050HS	GP1M009A050FSH	Unit
Drain-Source Voltage	V_{DSS}	500		V
Gate-Source Voltage	V_{GS}	±30		V
Continuous Drain Current $T_C = 25\text{ °C}$	I_D	8.5	8.5 *	A
		4.87	4.87 *	A
Pulsed Drain Current (Note 1)	I_{DM}	34	34 *	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	439		mJ
Repetitive Avalanche Current (Note 1)	I_{AR}	8.5		A
Repetitive Avalanche Energy (Note 1)	E_{AR}	12.7		mJ
Power Dissipation $T_C = 25\text{ °C}$	P_D	127	39	W
		1.01	0.31	W/°C
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5		V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150		°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	T_L	300		°C

* Limited only by maximum junction temperature

Thermal Characteristics

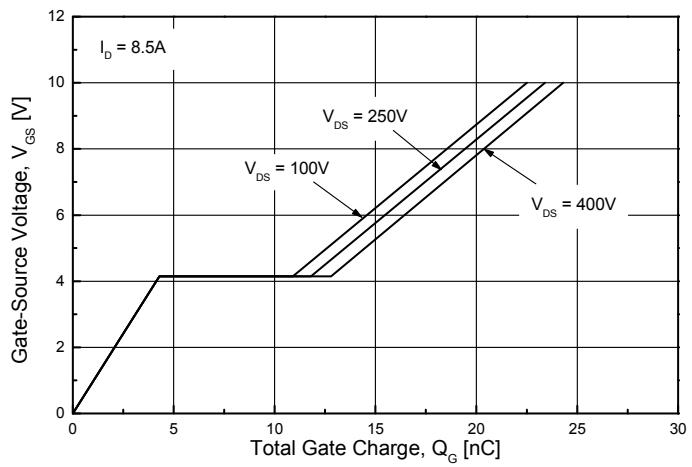
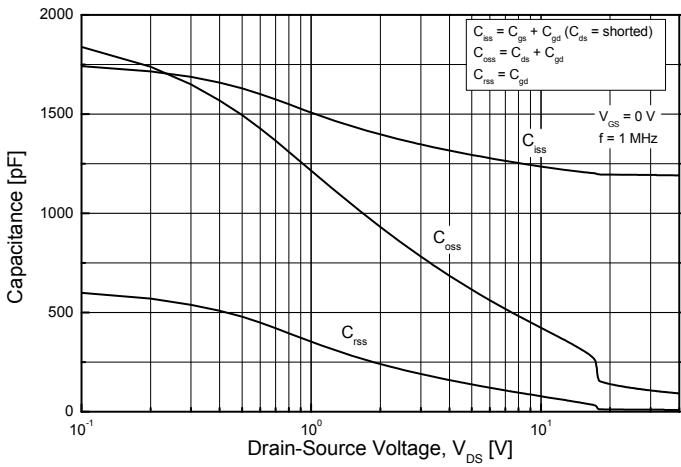
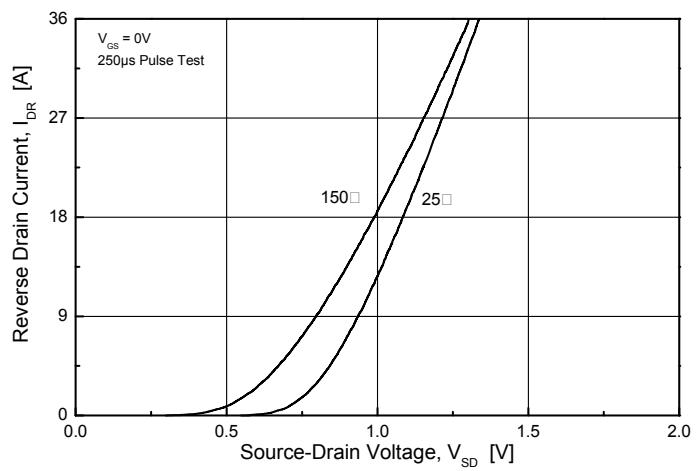
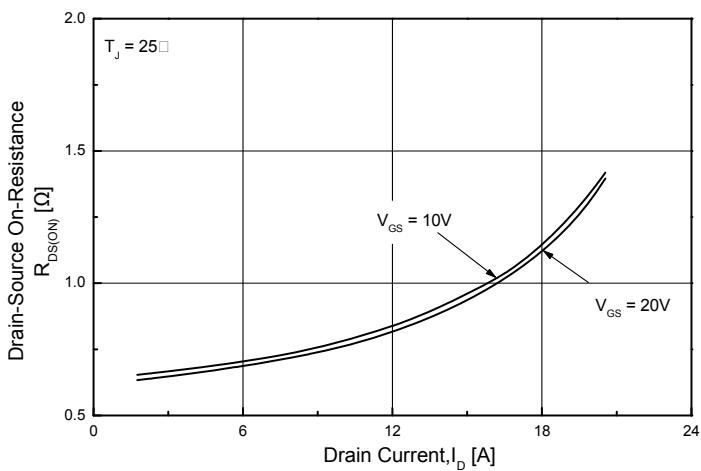
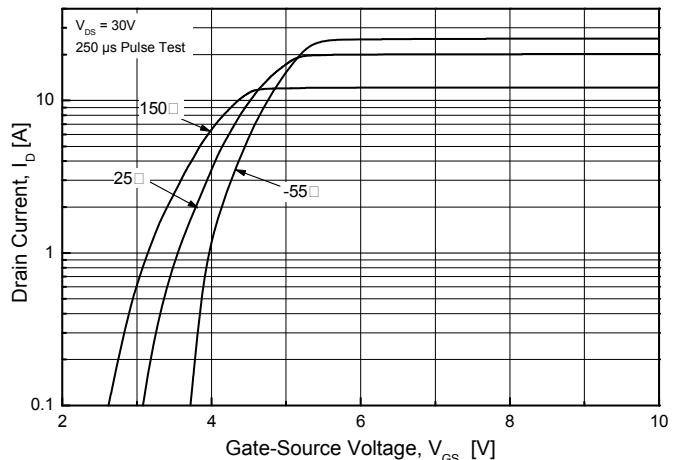
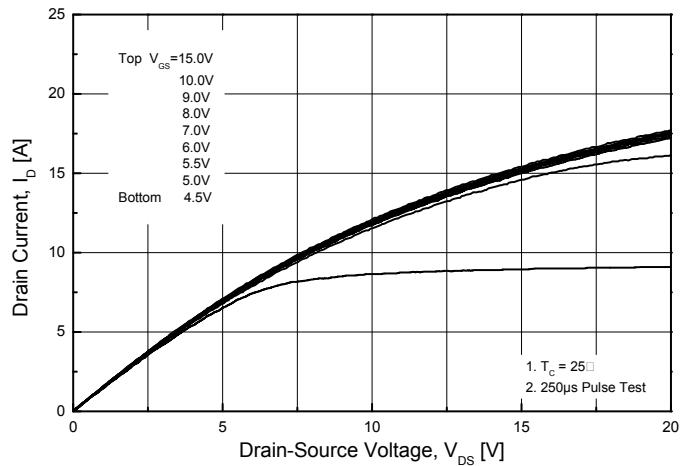
Parameter	Symbol	GP1M009A050HS	GP1M009A050FSH	Unit
Maximum Thermal resistance, Junction-to-Case	$R_{\theta JC}$	0.98	3.2	°C/W
Maximum Thermal resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	62.5	°C/W

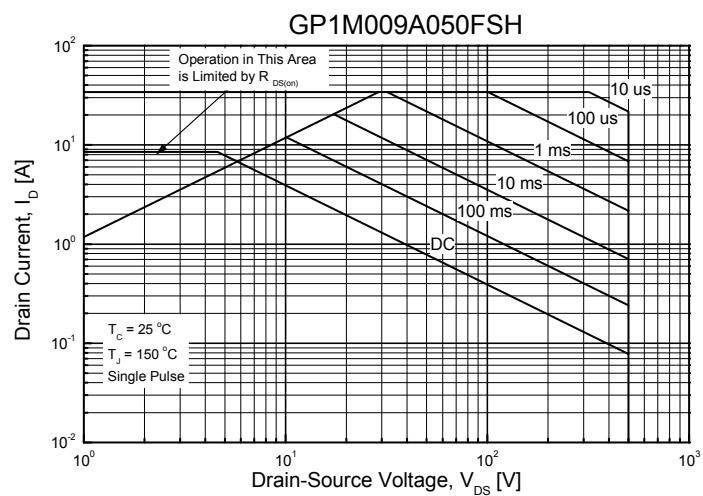
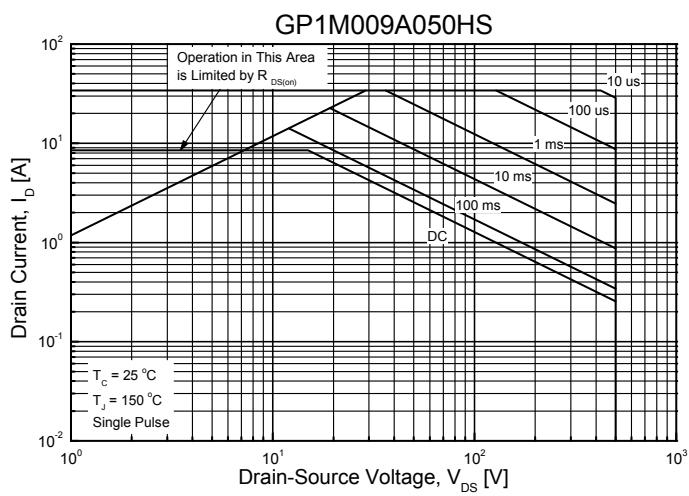
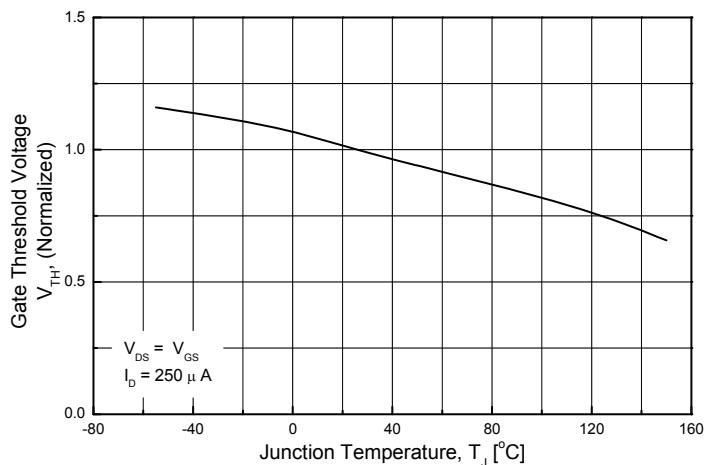
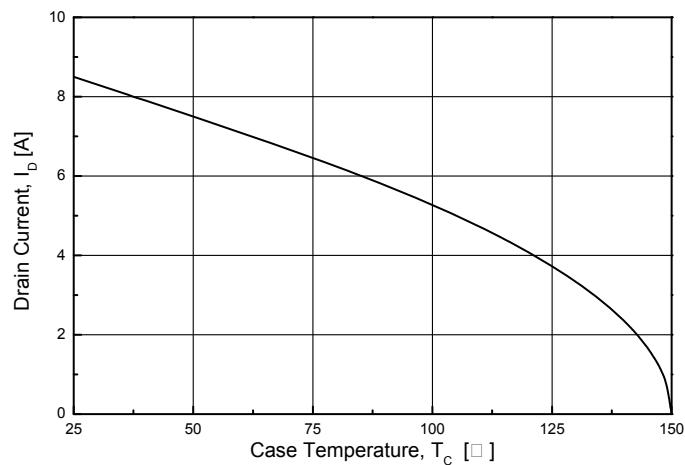
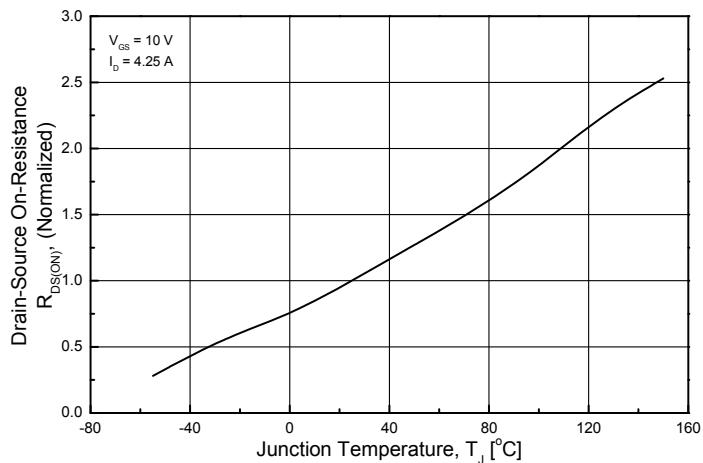
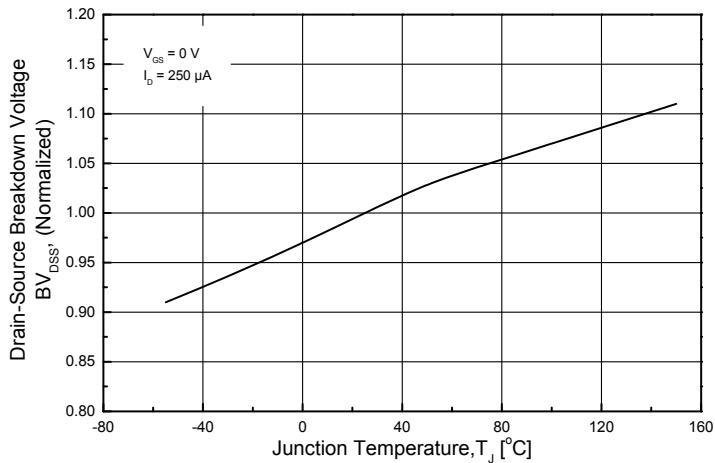
Electrical Characteristics : $T_C=25^\circ\text{C}$, unless otherwise noted

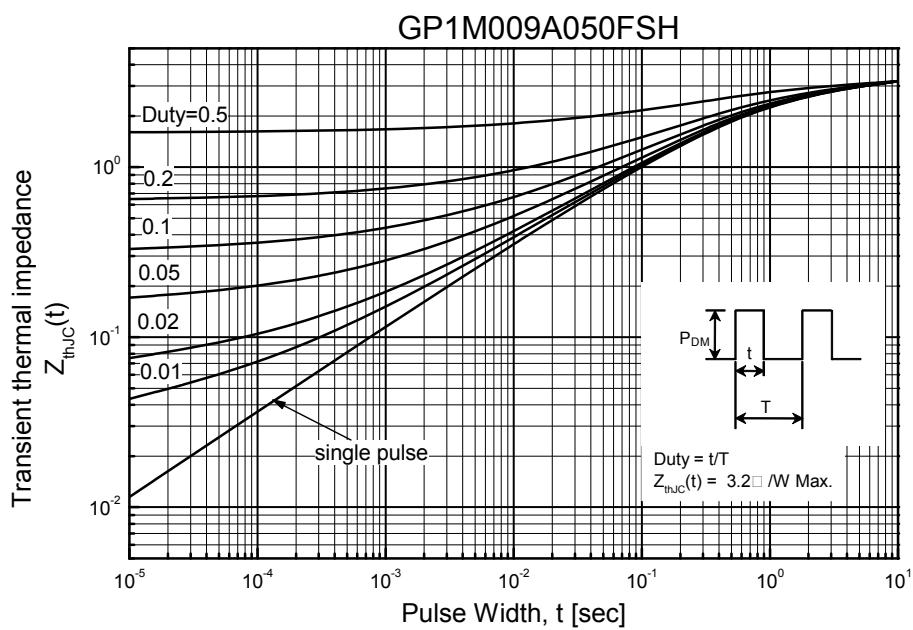
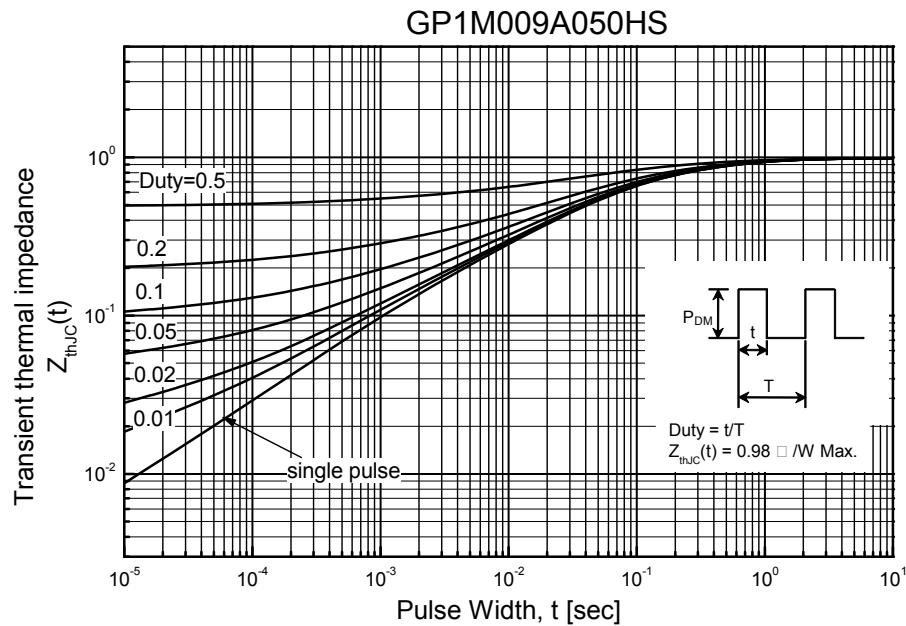
Parameter	Symbol	Test condition	Min	Typ	Max	Units
OFF						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0 \text{ V}, I_D = 250 \mu\text{A}$	500	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 500 \text{ V}, V_{\text{GS}} = 0 \text{ V}$	--	--	1	μA
		$V_{\text{DS}} = 400 \text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
Forward Gate-Source Leakage Current	I_{GSSF}	$V_{\text{GS}} = 30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	--	--	100	nA
Reverse Gate-Source Leakage Current	I_{GSSR}	$V_{\text{GS}} = -30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	--	--	-100	nA
ON						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250 \mu\text{A}$	2	--	4	V
Drain-Source On-Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 10 \text{ V}, I_D = 4.25 \text{ A}$	--	0.68	0.85	Ω
Forward Transconductance ^(Note 4)	g_{FS}	$V_{\text{DS}} = 30 \text{ V}, I_D = 4.25 \text{ A}$	--	13	--	S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 25 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1.0 \text{ MHz}$	--	1195	--	pF
Output Capacitance	C_{oss}		--	120	--	pF
Reverse Transfer Capacitance	C_{rss}		--	11	--	pF
SWITCHING						
Turn-On Delay Time ^(Note 4,5)	$t_{\text{d(on)}}$	$V_{\text{DD}} = 250 \text{ V}, I_D = 8.5 \text{ A}, R_G = 25 \Omega$	--	23	--	ns
Turn-On Rise Time ^(Note 4,5)	t_r		--	22	--	ns
Turn-Off Delay Time ^(Note 4,5)	$t_{\text{d(off)}}$		--	99	--	ns
Turn-Off Fall Time ^(Note 4,5)	t_f		--	28	--	ns
Total Gate Charge ^(Note 4,5)	Q_g	$V_{\text{DS}} = 400 \text{ V}, I_D = 8.5 \text{ A}, V_{\text{GS}} = 10 \text{ V}$	--	24	--	nC
Gate-Source Charge ^(Note 4,5)	Q_{gs}		--	4	--	nC
Gate-Drain Charge ^(Note 4,5)	Q_{gd}		--	9	--	nC
SOURCE DRAIN DIODE						
Maximum Continuous Drain-Source Diode Forward Current	I_s	----	--	--	8.5	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}	----	--	--	34	A
Drain-Source Diode Forward Voltage	V_{SD}	$V_{\text{GS}} = 0 \text{ V}, I_s = 8.5 \text{ A}$	--	--	1.5	V
Reverse Recovery Time ^(Note 4)	t_{rr}	$V_{\text{GS}} = 0 \text{ V}, I_s = 8.5 \text{ A}$ $dI_F / dt = 100 \text{ A}/\mu\text{s}$	--	172	--	ns
Reverse Recovery Charge ^(Note 4)	Q_{rr}		--	0.6	--	μC

Note :

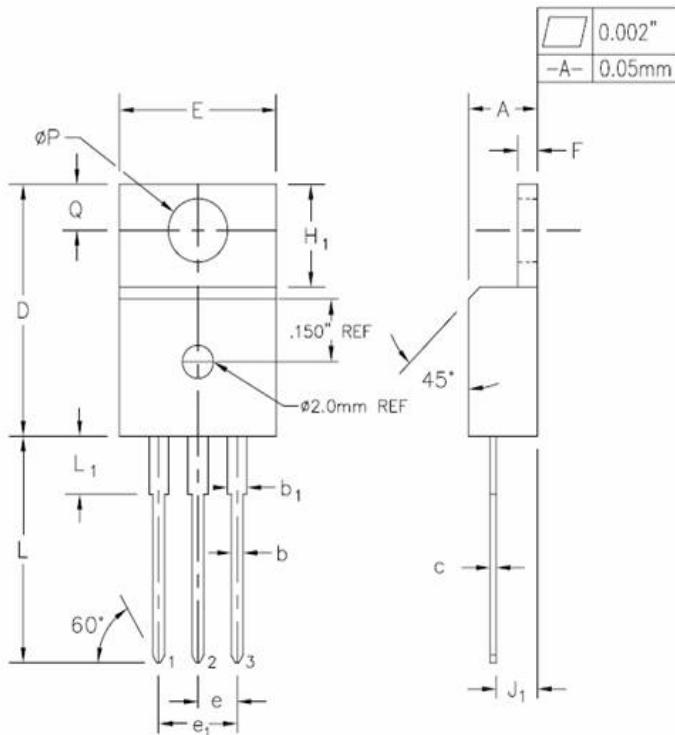
1. Repeated rating : Pulse width limited by safe operating area
2. L=10.9mH, $I_{AS} = 8.5\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 8.5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq \text{BV}_{DS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics





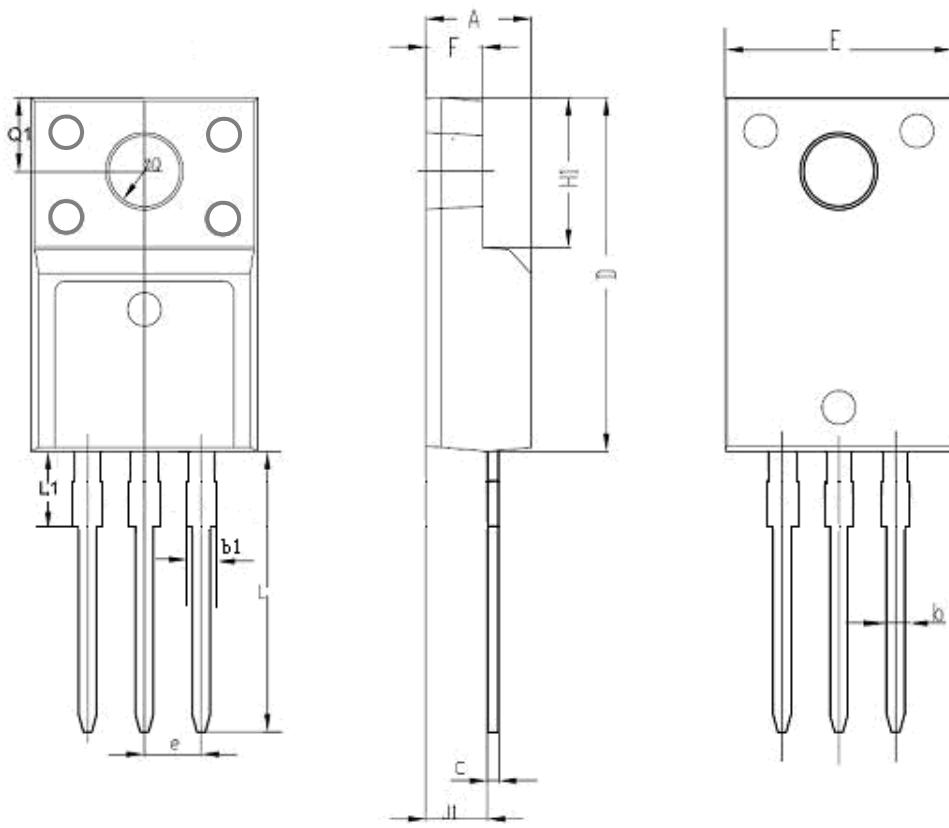


TO-220AB-3L MECHANICAL DATA



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	0.170	0.180	4.32	4.57	
b	0.028	0.036	0.71	0.91	
b ₁	0.045	0.055	1.15	1.39	
c	0.014	0.021	0.36	0.53	
D	0.590	0.610	14.99	15.49	
E	0.395	0.410	10.04	10.41	
e	0.100 TYP.		2.54 TYP.		
e ₁	0.200 BSC		5.08 BSC		
F	0.048	0.054	1.22	1.37	
H ₁	0.235	0.255	5.97	6.47	
J ₁	0.100	0.110	2.54	2.79	
L	0.530	0.550	13.47	13.97	
L ₁	0.130	0.150	3.31	3.81	2
φP	0.149	0.153	3.79	3.88	
Q	0.102	0.112	2.60	2.84	

TO-220F-3L MECHANICAL DATA



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.178	0.194	4.53	4.93	
b	0.028	0.036	0.71	0.91	
C	0.018	0.024	0.45	0.60	
D	0.617	0.633	15.67	16.07	
E	0.392	0.408	9.96	10.36	
e	0.100 TYP.		2.54TYP.		
H1	0.256	0.272	6.50	6.90	
J1	0.101	0.117	2.56	2.96	
L	0.503	0.519	12.78	13.18	
φQ	0.117	0.133	2.98	3.38	
b1	0.045	0.055	1.15	1.39	
L1	0.114	0.130	2.9	3.3	
Q1	0.122	0.138	3.10	3.50	
F	0.092	0.108	2.34	2.74	

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